

# High-Current Complementary Silicon Power Transistors

... designed for use in high-power amplifier and switching circuit applications.

- High Current Capability —  $I_C$  Continuous = 50 Amperes.
- DC Current Gain —  
 $h_{FE} = 15-60 @ I_C = 25 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage —  
 $V_{CE(sat)} = 1.0 \text{ Vdc (Max) @ } I_C = 25 \text{ Adc}$

## MAXIMUM RATINGS (1)

Rating	Symbol	2N5685	2N5684 2N5686	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	Vdc
Collector-Base Voltage	$V_{CB}$	60	80	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0		Vdc
Collector Current — Continuous	$I_C$	50		A <sub>dc</sub>
Base Current	$I_B$	15		A <sub>dc</sub>
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 1.715		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^\circ\text{C}$

## THERMAL CHARACTERISTICS (1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	0.584	$^\circ\text{C/W}$

(1) Indicates JEDEC Registered Data.

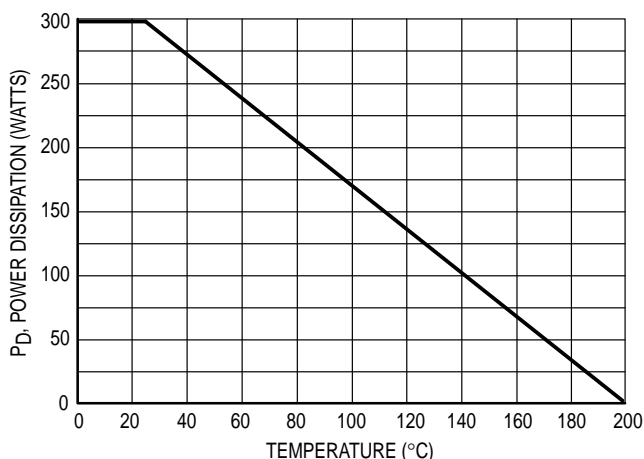


Figure 1. Power Derating

Safe Area Curves are indicated by Figure 5. All limits are applicable and must be observed.

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7

**PNP**  
**2N5684**  
**NPN**  
**2N5685**  
**2N5686\***

\*Motorola Preferred Device

**50 AMPERE**  
**COMPLEMENTARY**  
**SILICON**  
**POWER TRANSISTORS**  
**60-80 VOLTS**  
**300 WATTS**

**CASE 197A-05**  
**TO-204AE**

# 2N5684 2N5685 2N5686

\*ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage (Note 1) ( $I_C = 0.2 \text{ Adc}$ , $I_B = 0$ )	$V_{CE(sus)}$	60 80	—	Vdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 40 \text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	— —	1.0 1.0	mAdc
Collector Cutoff Current ( $V_{CE} = 60 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 80 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ ) ( $V_{CE} = 80 \text{ Vdc}$ , $V_{EB(off)} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ )	$I_{CEX}$	— — — —	2.0 2.0 10 10	mAdc
Collector Cutoff Current ( $V_{CB} = 60 \text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	— —	2.0 2.0	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	5.0	mAdc

## ON CHARACTERISTICS

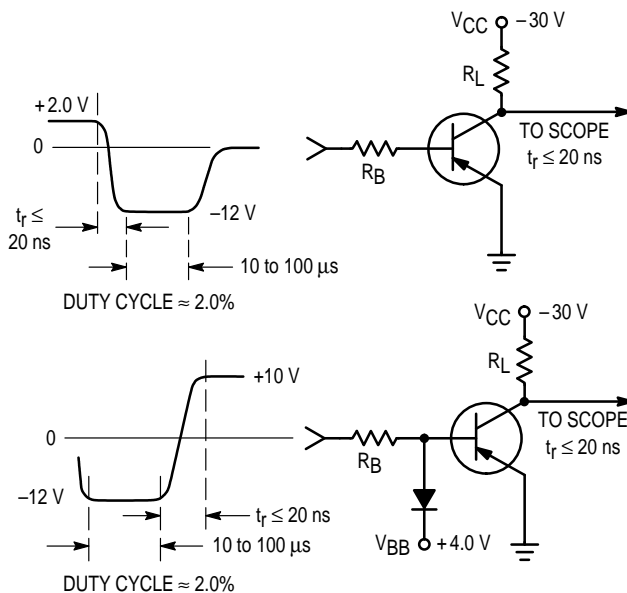
DC Current Gain (Note 1) ( $I_C = 25 \text{ Adc}$ , $V_{CE} = 2.0 \text{ Vdc}$ ) ( $I_C = 50 \text{ Adc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	$h_{FE}$	15 5.0	60 —	—
Collector–Emitter Saturation Voltage (Note 1) ( $I_C = 25 \text{ Adc}$ , $I_B = 2.5 \text{ Adc}$ ) ( $I_C = 50 \text{ Adc}$ , $I_B = 10 \text{ Adc}$ )	$V_{CE(sat)}$	— —	1.0 5.0	Vdc
Base–Emitter Saturation Voltage (Note 1) ( $I_C = 25 \text{ Adc}$ , $I_B = 2.5 \text{ Adc}$ )	$V_{BE(sat)}$	—	2.0	Vdc
Base–Emitter On Voltage (Note 1) ( $I_C = 25 \text{ Adc}$ , $V_{CE} = 2.0 \text{ Vdc}$ )	$V_{BE(on)}$	—	2.0	Vdc

## DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 5.0 \text{ Adc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )	$f_T$	2.0	—	MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 0.1 \text{ MHz}$ )	$C_{ob}$	— —	2000 1200	pF
Small–Signal Current Gain ( $I_C = 10 \text{ Adc}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	$h_{fe}$	15	—	

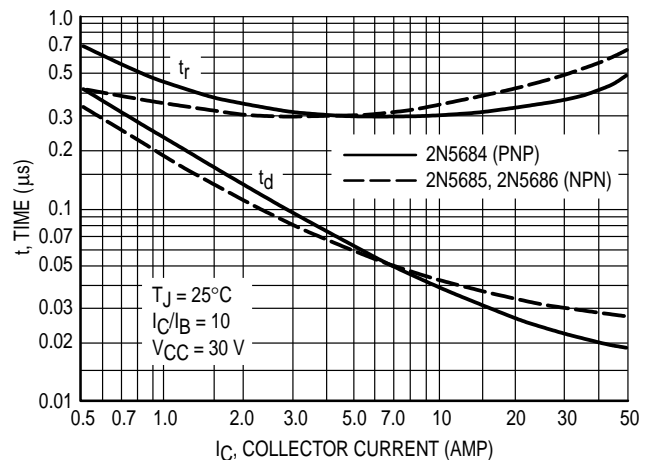
\* Indicates JEDEC Registered Data.

Note 1: Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



FOR CURVES OF FIGURES 3 & 6,  $R_B$  &  $R_L$  ARE VARIED.  
INPUT LEVELS ARE APPROXIMATELY AS SHOWN.  
FOR NPN CIRCUITS, REVERSE ALL POLARITIES.

**Figure 2. Switching Time Test Circuit**



**Figure 3. Turn–On Time**

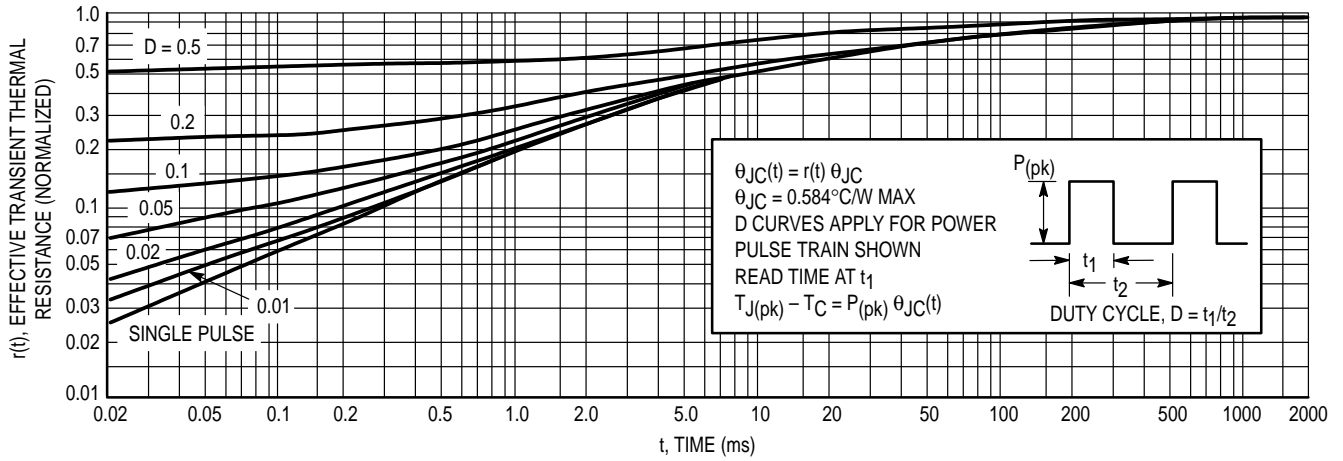


Figure 4. Thermal Response

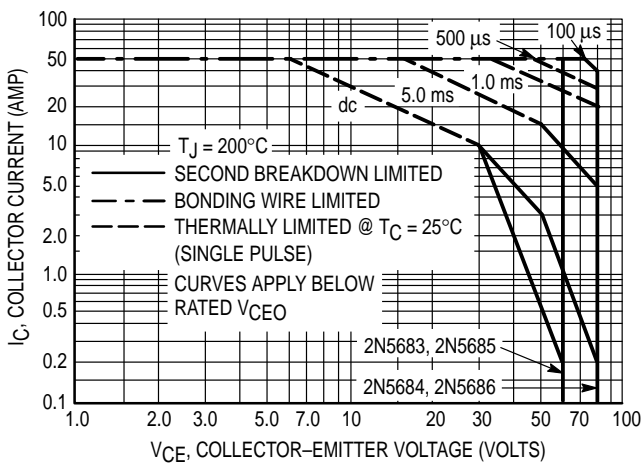


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 200^{\circ}\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 200^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

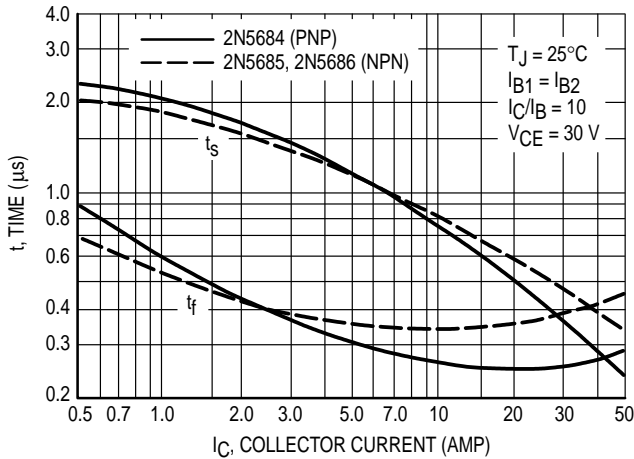


Figure 6. Turn-Off Time

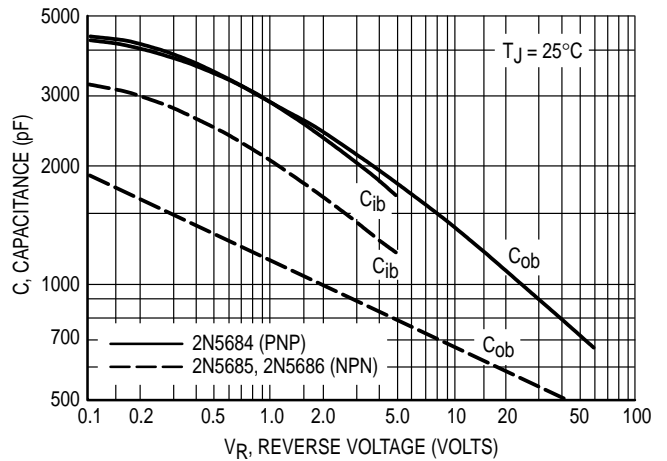


Figure 7. Capacitance

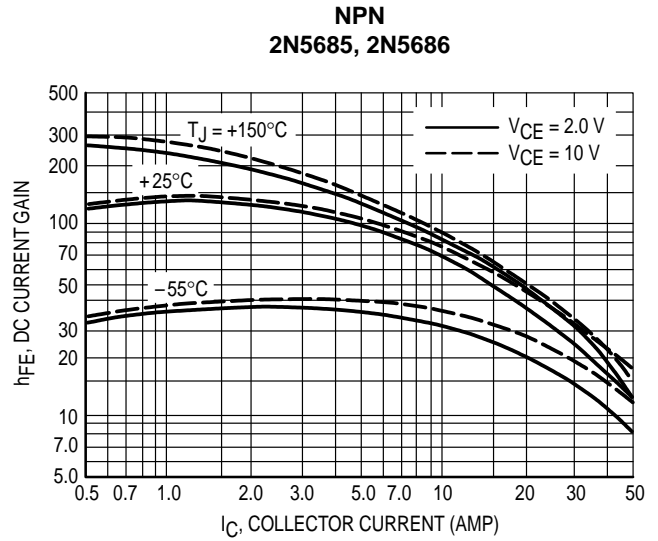
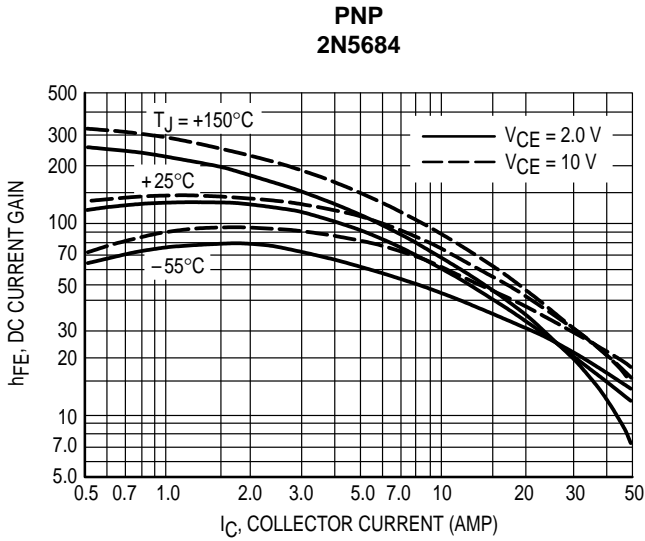


Figure 8. DC Current Gain

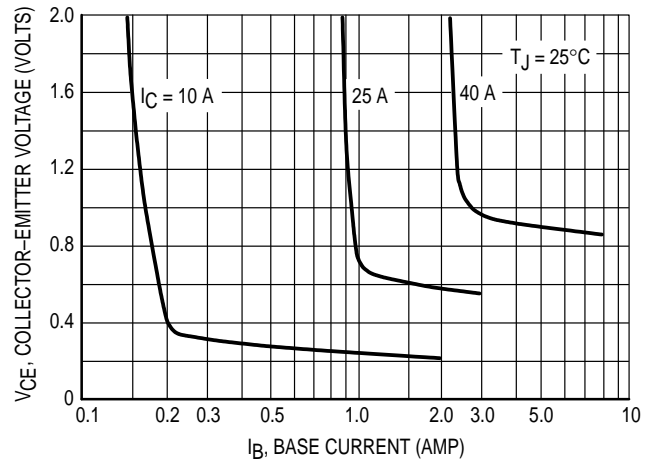
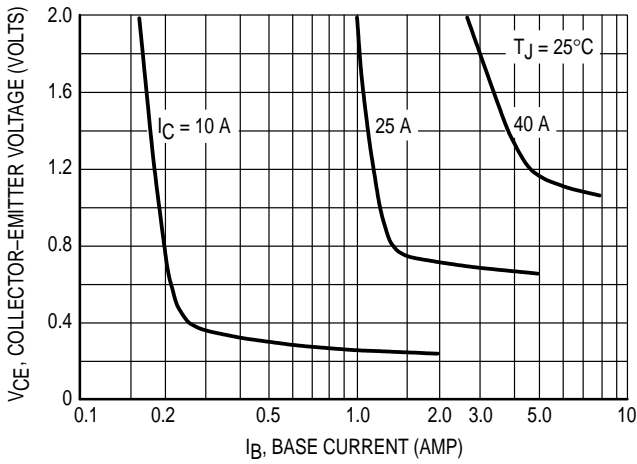


Figure 9. Collector Saturation Region

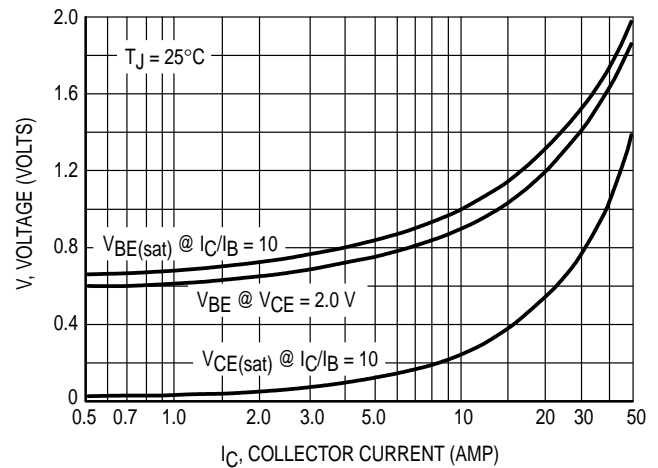
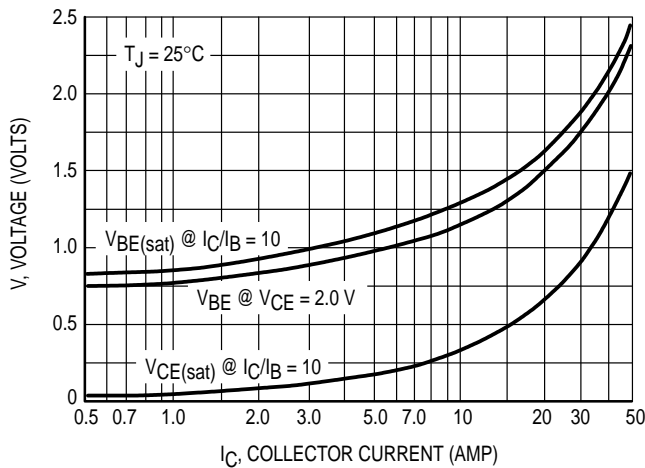
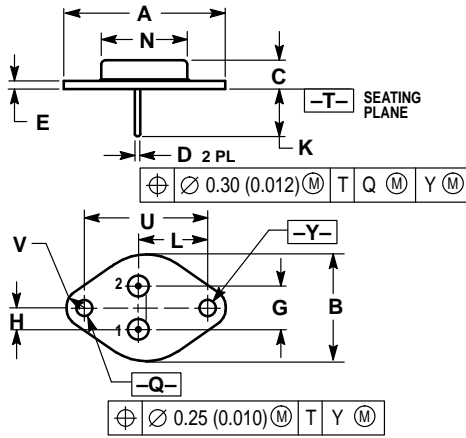


Figure 10. "On" Voltages

PACKAGE DIMENSIONS



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.530 REF		38.86 REF	
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:  
 PIN 1: BASE  
 2: EMITTER  
 CASE: COLLECTOR

CASE 197A-05  
 TO-204AE  
 ISSUE J

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